

# RELIABILITY MONITOR

PRODUCT	MONITOR DATE	DATE CODE	ASSEMBLY FACILITY	ASSEMBLY LOT NO	PROCESS TYPE	PACKAGE TYPE
DS2502	Jun-96	9620 A6	ANAM, K.	DN546229ATA	1.2μ OX/NI EPROM	08 SOIC 150

**STRESS/JOB NO.**

**READPOINT  
(Sample Size/No. of Fails)**

Preconditioning (P/C):  
HTC Vapor Phase  
P-17868

<u>Electrical</u>	<u>Cum %</u>
233/2	0.9%
F1	

Infant / High Voltage Life  
125°C, 7.0 V.  
P-17946, P-17967

<u>0 Hr</u>	<u>48 Hr</u>	<u>336 Hr</u>	<u>1KHr</u>	<u>*Failure Rate</u>
231/1	223/0	77/0	77/0	30 Fits
F2				

Write Data

\*Chi Squared Method, 60% C. L., 55°C & 5.5V; Temperature Derating: Ea = 0.7 ev; Voltage Derating B = 1.0

Temp Cycle  
-55°C to +125°C  
P-17968

<u>300 ~</u>	<u>1K ~</u>	<u>Cum %</u>
35/1	34/0	2.9%
F3		

Biased Moisture  
85°C/85% RH, 5.5 V.  
P-17969

<u>274 Hr</u>	<u>959 Hr</u>	<u>Cum %</u>
77/0	77/0	0.0%

Storage Life  
150°C, No bias  
P-17970

<u>336 Hr</u>	<u>1KHr</u>	<u>Cum %</u>
34/0	34/0	0.0%

**Failure Mode**

F1: 2-IO resistance  
F2: 1-DQ resistance

**Failure Analysis**

In process  
In process

**Failure Mode**

F3: 1-DQ resistance

**Failure Analysis**

In process